

MICROWAVE LOW NOISE AMPLIFIER
NPN SILICON EPITAXIAL TRANSISTOR
(WITH BUILT-IN 2 ELEMENTS) MINI MOLD

FEATURES

- Low Noise, High Gain
- Operable at Low Voltage
- Small Feed-back Capacitance
 $C_{re} = 0.4$ pF TYP.
- Built-in 2 Transistors ($2 \times 2SC4959$)

ORDERING INFORMATION

PART NUMBER	QUANTITY	PACKING STYLE
μ PA806T	Loose products (50 PCS)	Embossed tape 8 mm wide. Pin 6 (Q1 Base), Pin 5 (Q2 Base), Pin 4 (Q2 Emitter) face to perforation side of the tape.
μ PA806T-T1	Taping products (3 KPCS/Reel)	

Remark If you require an evaluation sample, please contact an NEC Sales Representative. (Unit sample quantity is 50 pcs.)

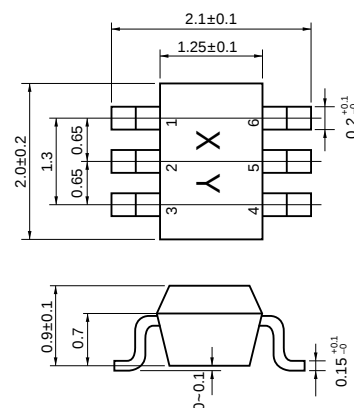
ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

PARAMETER	SYMBOL	RATING	UNIT
Collector to Base Voltage	V_{CBO}	9	V
Collector to Emitter Voltage	V_{CEO}	6	V
Emitter to Base Voltage	V_{EBO}	2	V
Collector Current	I_C	30	mA
Total Power Dissipation	P_T	150 in 1 element 200 in 2 elements ^{Note}	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-65 to +150	$^\circ\text{C}$

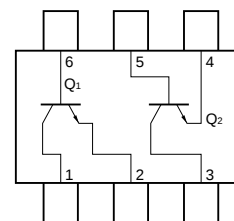
Note 110 mW must not be exceeded in 1 element.

PACKAGE DRAWINGS

(Unit: mm)



PIN CONFIGURATION (Top View)



PIN CONNECTIONS

1. Collector (Q1)
2. Emitter (Q1)
3. Collector (Q2)
4. Emitter (Q2)
5. Base (Q2)
6. Base (Q1)

ELECTRICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$)

PARAMETER	SYMBOL	CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cutoff Current	I_{CBO}	$V_{CB} = 5\text{ V}, I_E = 0$			0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 1\text{ V}, I_C = 0$			0.1	μA
DC Current Gain	h_{FE}	$V_{CE} = 3\text{ V}, I_C = 10\text{ mA}$ Note 1	75		150	
Gain Bandwidth Product	f_T	$V_{CE} = 3\text{ V}, I_C = 10\text{ mA}, f = 2\text{ GHz}$		12		GHz
Feed-back Capacitance	C_{re}	$V_{CB} = 3\text{ V}, I_E = 0, f = 1\text{ MHz}$ Note 2		0.4	0.7	pF
Insertion Power Gain	$ S_{21} ^2$	$V_{CE} = 3\text{ V}, I_C = 10\text{ mA}, f = 2\text{ GHz}$	7	8.5		dB
Noise Figure	NF	$V_{CE} = 3\text{ V}, I_C = 3\text{ mA}, f = 2\text{ GHz}$		1.5	2.5	dB
h_{FE} Ratio	h_{FE1}/h_{FE2}	$V_{CE} = 3\text{ V}, I_C = 10\text{ mA}$ A smaller value among h_{FE} of $h_{FE1} = Q1, Q2$ A larger value among h_{FE} of $h_{FE2} = Q1, Q2$	0.85			

Notes 1. Pulse Measurement: $P_w \leq 350\text{ }\mu\text{s}$, Duty cycle $\leq 2\%$

2. Measured with 3-pin bridge, emitter and case should be connected to guard pin of bridge.

 h_{FE} CLASSIFICATION

Rank	KB
Marking	T83
h_{FE} Value	75 to 150

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$)